

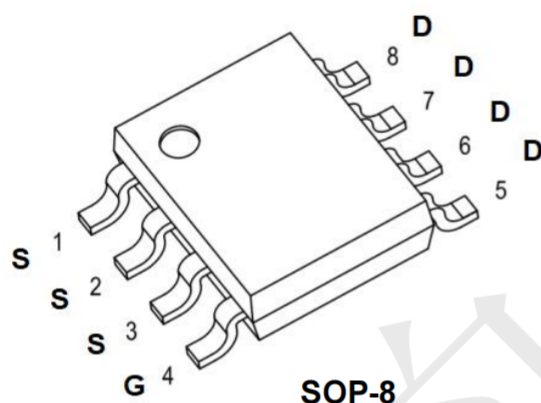
Product Summary

- V_{DS} 20 V
- I_{DS} (@ $V_{GS}=4.5V$) 20A
- $R_{DS(ON)}$ (@ $V_{GS}=4.5V$) < 4.8mΩ(Typ)

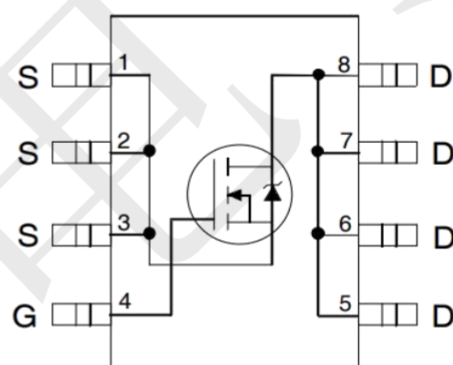
Application

- LED applications
- Synchronous Rectifiers for SMPS
- Power management
- PWM Application

Package and Pin Configuration



Circuit diagram



Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current $T_A=25^{\circ}C$	I_D	20	A
Continuous Drain Current $T_A=100^{\circ}C$	I_D	11	A
Pulsed Drain Current (note1)	I_{DM}	80	A
Single Pulse Avalanche Energy $L=8.7mH$, $I_{AS}=6A$	EAS	48	mJ
Maximum Power Dissipation $T_C=25^{\circ}C$	P_D	38	W
Operating Junction Temperature Range	T_J	-55 to +150	$^{\circ}C$
Storage Temperature Range	T_{stg}	-55 to +150	$^{\circ}C$

Thermal Characteristic

PARAMETER	Symbol	Value	Unit
Thermal Resistance Junction-ambient	$R_{\theta JA}$	39	$^{\circ}C/W$
Thermal Resistance Junction-Case	$R_{\theta JC}$	4.2	$^{\circ}C/W$

notes 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. When mounted on 1" square PCB (FR4 material).

Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	BV_{DSS}	20	--	--	V
Gate-Source Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	$V_{GS(th)}$	0.4	0.7	1.0	V
Gate-Source Leakage	$V_{DS}=0V, V_{GS}=\pm 12V$	I_{GSS}	--	--	± 100	nA
Zero Gate Voltage Drain Current	$V_{DS}=20V, V_{GS}=0V$	I_{DSS}	--	--	1	μA
	$V_{DS}=20V, T_J=85^{\circ}C$		--	--	10	μA
Drain-Source On-State Resistance (Note 1)	$V_{GS}=4.5V, I_D=10A$	$R_{DS(on)}$	--	4.8	6.6	m Ω
	$V_{GS}=2.5V, I_D=5A$		--	6.8	10	m Ω
Forward Transconductance (Note 2)	$V_{DS}=10V, I_D=10A$	g_{fs}	--	10	--	S
Dynamic (Note 2)						
Total Gate Charge (Note 3)	$V_{DS}=10V,$ $I_D=10A,$ $V_{GS}=4.5V$	Q_g	--	23	--	nC
Gate-Source Charge (Note 3)		Q_{gs}	--	4.5	--	
Gate-Drain Charge (Note 3)		Q_{gd}	--	7.2	--	
Input Capacitance	$V_{DS}=10V,$ $V_{GS}=0V,$ $F=1.0MHz$	C_{iss}	--	1830	--	pF
Output Capacitance		C_{oss}	--	290	--	
Reverse Transfer Capacitance		C_{rss}	--	270	--	
Switching						
Turn-On Delay Time (Note 3)	$V_{DD}=20V,$ $I_D=10A,$ $V_{GS}=4.5V,$ $R_G=3.3\Omega$	$t_{d(on)}$	--	15	--	nS
Rise Time (Note 3)		t_r	--	36	--	
Turn-Off Delay Time (Note 3)		$t_{d(off)}$	--	50	--	
Fall Time (Note 3)		t_f	--	20	--	
Source-Drain Diode Ratings and Characteristics (Note 2)						
Forward Voltage	$V_{GS}=0V, I_{SD}=10A$	V_{SD}	--	0.7	1.2	V
Continuous Source Current	Integral reverse diode in the MOSFET	I_S	--	--	20	A
Pulsed Current (Note 1)		I_{SM}	--	--	80	A

Notes:

1. Pulse test; pulse width ≤ 300 μS, duty cycle ≤ 2%.
2. Guaranteed by design, not subject to production testing.
3. Independent of operating temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Figure1: Output Characteristics

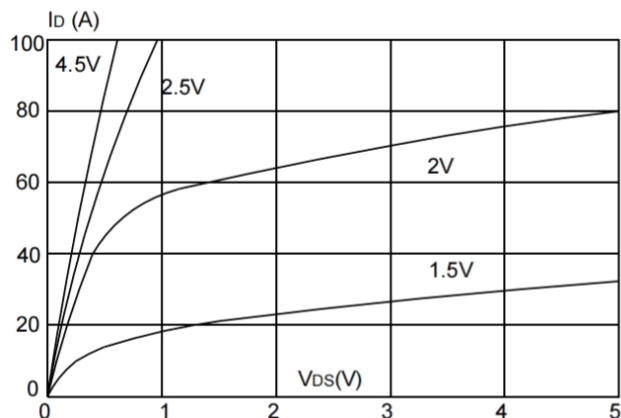


Figure 2: Typical Transfer Characteristics

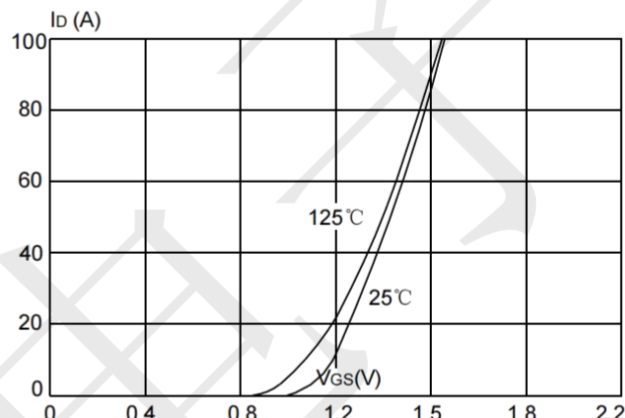


Figure 3: On-resistance vs. Drain Current

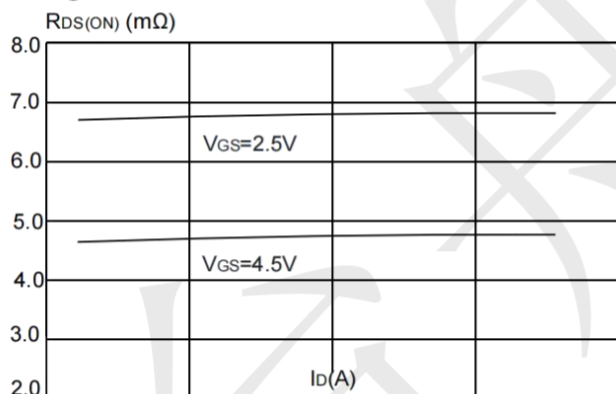


Figure 4: Body Diode Characteristics

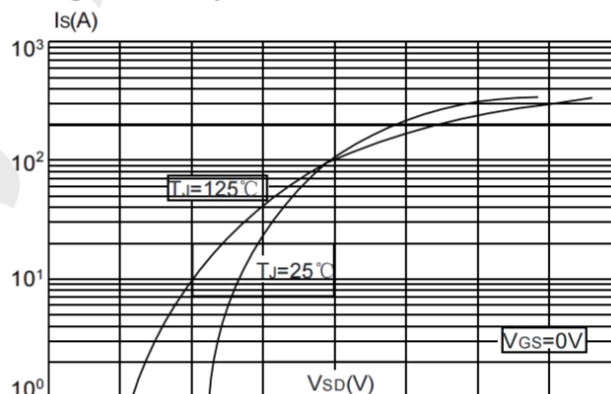


Figure 5: Normalized Breakdown Voltage vs. Junction Temperature

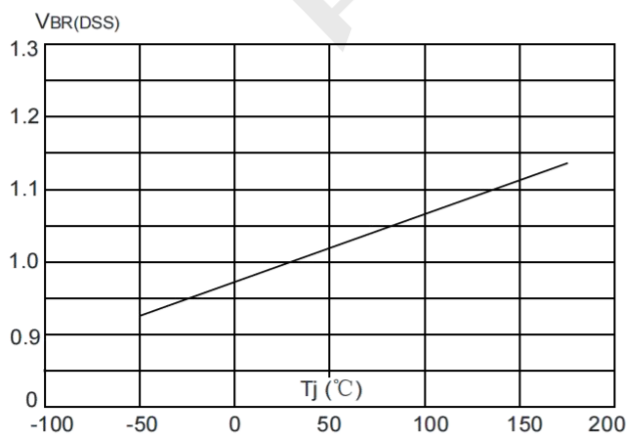
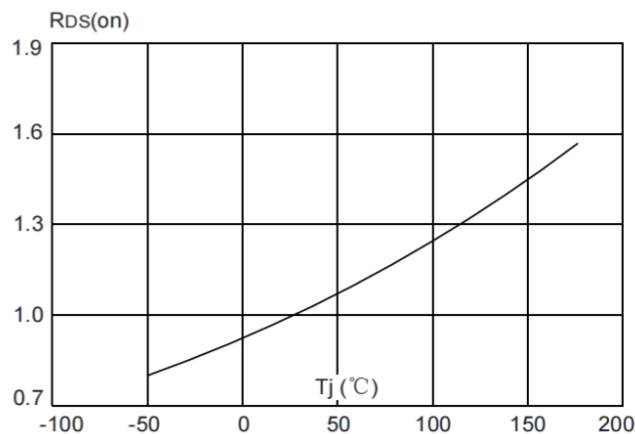
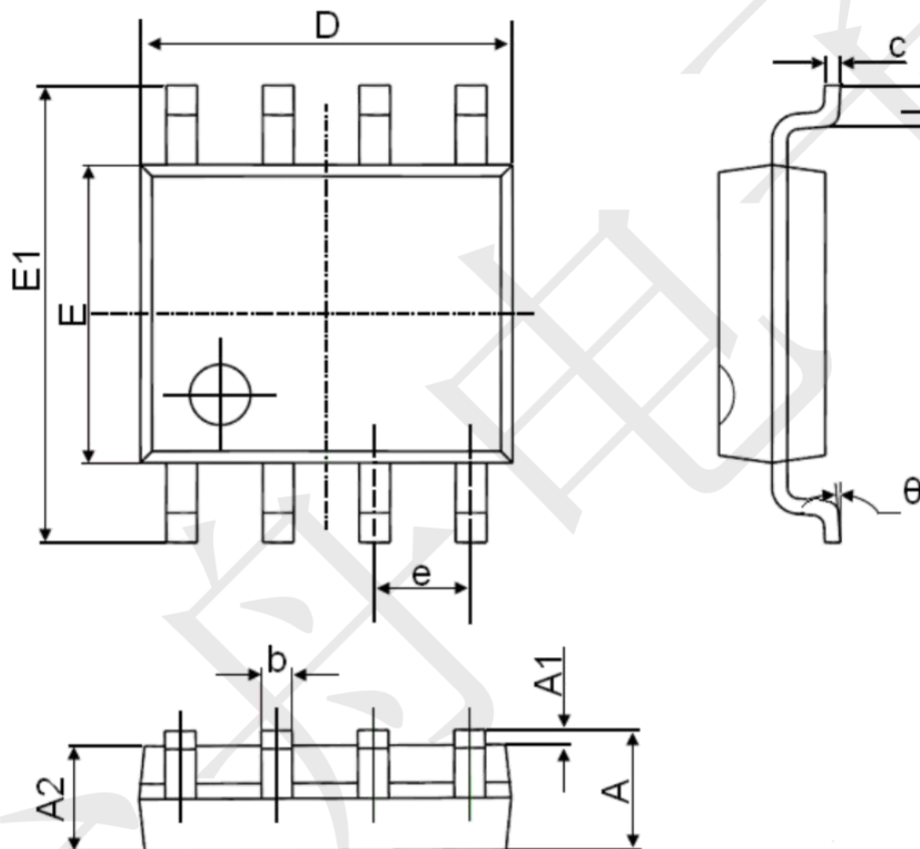


Figure 6: Normalized on Resistance vs. Junction Temperature



Package Information

SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°